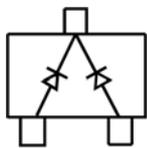
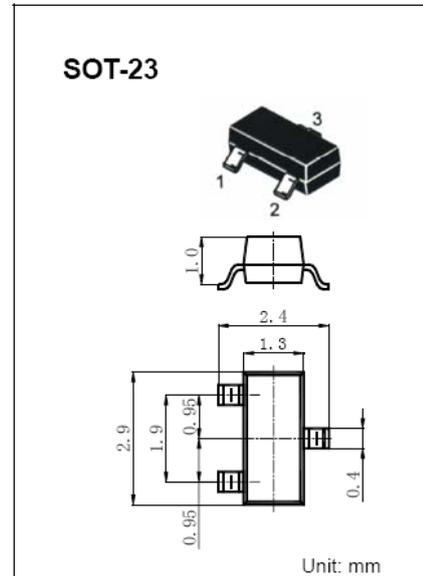


FEATURES

- Power dissipation, P_D : 225 mW ($T_{amb}=25^\circ\text{C}$)
- Forward Current, I_F : 200 mA
- Reverse Voltage, V_R : 70V
- Operating and storage junction temperature range:
 T_J, T_{stg} : -55°C to $+150^\circ\text{C}$
- SOT-23 Plastic-Encapsulate package



Device Making: A4



ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu\text{A}$	70		V
Reverse voltage leakage current	I_R	$V_R = 70\text{V}$		2.5	μA
Forward voltage	V_F	$I_F = 1\text{mA}$ $I_F = 10\text{mA}$ $I_F = 50\text{mA}$ $I_F = 150\text{mA}$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R = 0\text{V}, f = 1\text{MHz}$		1.5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10\text{mA}$ $I_R = 1\text{mA}, V_R = 5\text{V}$ $R_C = 100\Omega$		6	nS

Note: Unless otherwise specified, these specifications apply over the operating ambient temperature of 25°C .

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